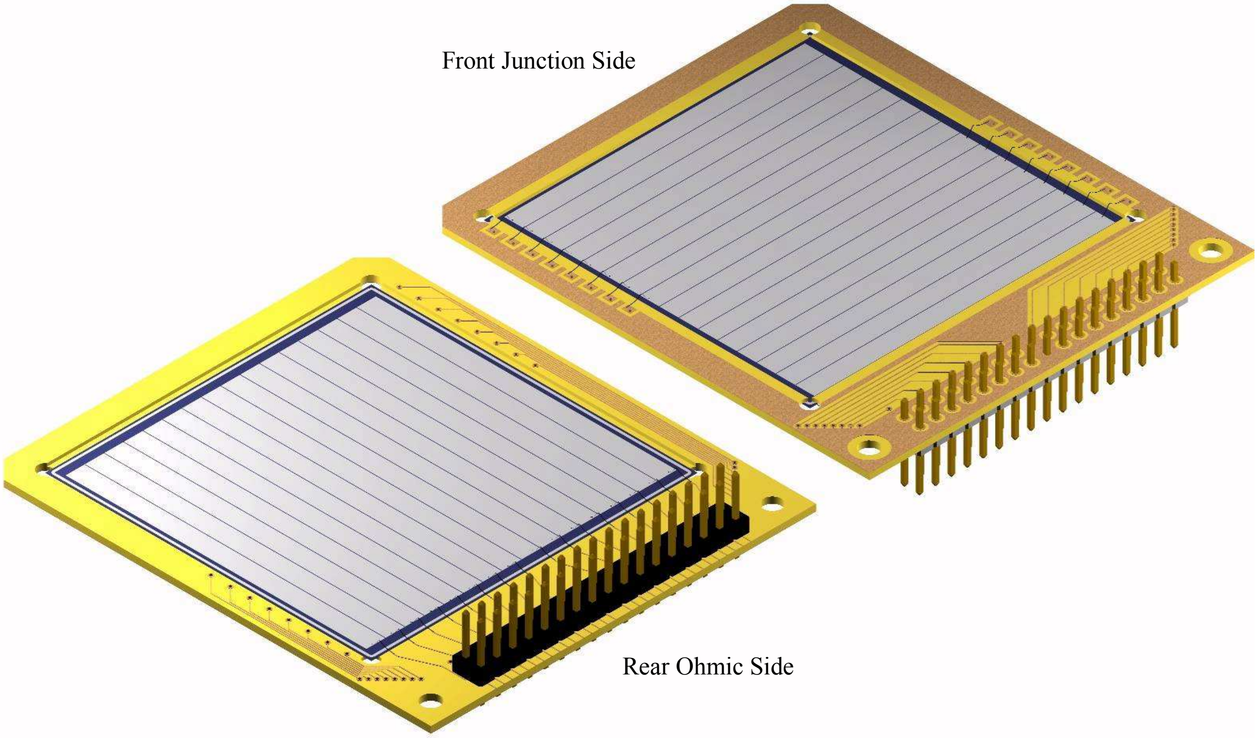
DESIGN W1

SPECIALIST DETECTORS FOR NUCLEAR PHYSICS

SILICON DETECTOR TYPE: TOTALLY DEPLETED SINGLE OR DOUBLE SIDED DC MICROSTRIP.
TECHNOLOGY: 4 INCH SILICON



Nº JUNCTION ELEMENTS: 16
Nº OHMIC ELEMENTS: 16
ELEMENT LENGTH: 49.5 mm
ELEMENT PITCH: 3.1 mm
ELEMENT WIDTH: 3000.0 µm
ACTIVE AREA: 50.0 x 50.0 mm^2
CHIP DIMENSIONS: 52.25 x 52.25 mm^2
53.78 x 53.78 mm^2
THICKNESS: 65, 80, 140, 250, 300, 500, 1000 and 1500 µm
WINDOW: Junction: Available with Standard or Thin window optical or nuclear device.
Ohmic: Standard

FULL DEPLETION VOLTAGE: 10 – 300 V subject to thickness selection
TOTAL CURRENT (FD): 1 – 2 µA
ELEMENT DARK CURRENT: 50 nA typically, 150 nA maximum
NOMINAL STRIP RESISTANCE: 100 MΩ
TOTAL ALPHA RESOLUTION: 55 keV Typical
METALLISATION: Aluminum 3000 Å
Junction: Available with 3% metal grid or as standard
Ohmic: Standard
PACKAGE: PCB with edge connections on one side.
Special ‘LASSA’ kapton with frame
Osaka PCB
CONNECTORS: Single row unshrouded vertical or 90^o pin header.
ACCEPTANCE: 100 %

QUALITY ASSURANCE: ISO9001